

Vishay High Power Products

Fast Recovery Diodes (Stud Version), 6/12/16 A

FEATURES

- · Short reverse recovery time
- Low stored charge
- Wide current range
- Excellent surge capabilities
- Standard JEDEC types
- Stud cathode and stud anode versions
- · Fully characterized reverse recovery conditions
- RoHS compliant

TYPICAL APPLICATIONS

- DC power supplies
- Inverters
- Converters
- Choppers
- Ultrasonic systems
- Freewheeling diodes

MAJOR R	MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	1N3879. TO 1N3883.	1N3889. TO 1N3893.	6FL	12FL	16FL	UNITS	
I _{F(AV)}	T _C = 100 °C	6 (1)	12 ⁽¹⁾	6	12	16	А	
I _{F(RMS)}		9.5	19	9.5	19	25	А	
	50 Hz	72	145	110	145	180		
I _{FSM}	60 Hz	75 ⁽¹⁾	150 ⁽¹⁾	115	150	190	A	
121	50 Hz	26	103	60	103	160	A 2 -	
l ² t	60 Hz	23	94	55	94	150	A ² s	
l²√t		363	856	1452	1452	2290	l²√s	
V _{RRM}	Range	50 to	V					
t _{rr}			ns					
TJ	Range		°C					

Note

(1) JEDEC registered values

PRODUCT SUMMARY

I_{F(AV)}

DO-203AA (DO-4)

6/12/16 A



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ELECTRICAL SPECIFICATIONS

VOLTAG	VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 25 °C μA	I _{RRM} MAXIMUM AT T _J = 100 °C mA	I _{RRM} MAXIMUM AT T _J = 150 °C mA			
1N3879.		50	75						
1N3880.		100	150						
1N3881.	-	200	250	15 ⁽¹⁾	1.0 ⁽¹⁾	3.0 (1)			
1N3882.		300	350						
1N3883.		400	450						
1N3889.		50	75						
1N3890.		100	150		3.0 (1)	5.0 ⁽¹⁾			
1N3891.	-	200	250	25 ⁽¹⁾					
1N3892.		300	350						
1N3893.		400	450						
	5	50	75						
	10	100	150						
6FL	20	200	275						
12FL	40	400	500	50	-	6.0			
16FL	60	600	725	1					
	80	800	950						
	100	1000	1250	1					

Note

(1) JEDEC registered values

FORWARD CONDUCTION									
PARAMETER	SYMBOL	TEST CONDITIONS			1N3879. 1N3883.	6FL	1N3889. 1N3893. 12FL	16FL	UNITS
Maximum average forward current	Irano	180° condu	uction, half sine	wave	6 ⁽¹⁾	6	12 ⁽¹⁾	16	Α
at case temperature	I _{F(AV)}	DC			100	100	100	100	°C
Maximum RMS current	I _{F(RMS)}				9.5	9.5	19	25	
		t = 10 ms	No voltage	Sinusoidal half wave, initial T _J = 150 °C	85	130	170	215	A
Maximum peak, one-cycle	I _{FSM}	t = 8.3 ms	reapplied		90	135	180	225	
non-repetitive forward current		t = 10 ms	100 % V _{RRM}		72	110	145	180	
		t = 8.3 ms	reapplied		75 ⁽¹⁾	115	150 ⁽¹⁾	190	
		t = 10 ms	No voltage		36	86	145	230	
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied		33	78	130	210	A ² s
Maximum - tior fusing		t = 10 ms	100 % V _{RRM}		26	60	103	160	A-S
		t = 8.3 ms	reapplied		23	55	94	150	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied			363	856	1452	2290	A²√s
Maximum forward voltage drop	V _{FM}	$T_J = 25 \text{ °C}; I_F = \text{Rated } I_{F(AV)} \text{ (DC)}$			1.4 ⁽¹⁾	1.4	1.4 ⁽¹⁾	1.4	V
waximum forward voltage drop		T _C = 100 °	T_{C} = 100 °C; I_{FM} = π x rated $I_{F(AV)}$			1.5	1.5 ⁽¹⁾	1.5	V

Note

⁽¹⁾ JEDEC registered values



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RECOVERY	RECOVERY CHARACTERISTICS									
PARAMETER	SYMBOL	BOL TEST CONDITIONS		1N3889. 1N3893.	6FL 12FL 16FL		UNITS			
					S02	S05				
Maximum reverse	+	$T_J = 25 \text{ °C}, I_F = 1 \text{ A to } V_R = 30 \text{ V},$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	150	150	-	-	ns	I _{FM}		
recovery time	t _{rr}	$T_J = 25 \text{ °C}, dI_F/dt = 25 \text{ A/}\mu\text{s},$ $I_{FM} = \pi \text{ x rated } I_{F(AV)}$	300 (1)	300 (1)	200	500	115			
Maximum peak recovery current	I _{RM(REC)}	$I_{FM} = \pi x \text{ rated } I_{F(AV)}$	4 (1)	5 (1)		-	-	dir/ dt/ I _{RM(REC)}		
Maximum reverse	0	$T_J = 25 \text{ °C}, I_F = 1 \text{ A to } V_R = 30 \text{ V},$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	400	350	-	-	nC			
recovery charge	Q _{rr}	$T_J = 25 \text{ °C}, dI_F/dt = 25 \text{ A}/\mu \text{s},$ $I_{FM} = \pi \text{ x rated } I_{F(AV)}$	400	400	-	-	10			

Note

(1) JEDEC registered values

THERMAL AND MECHANI	THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	1N3879. 1N3883. 6FL	1N3889. 1N3893. 12FL	16FL	UNITS		
Maximum junction operating temperature range	TJ	TJ		- 65 to 150				
Maximum storage temperature range	T _{Stg}		- 65 to 175					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	2.5	2.0	1.6	°C/W		
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased 0.5				C/VV		
		Not lubricated threads	1.5 ^{+ 0 - 10 %} (13)			N ⋅ m (lbf ⋅ in)		
Allowable mounting torque		Lubricated threads	1.2 ^{+ 0 - 10} % (10)					
Approximate weight			7			g		
Approximate weight			0.25			oz.		
Case style		JEDEC		DO-203A	A (DO-4)			

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CONDUCTION ANGLE	1N3879. 1N3883. 6FL	1N3889. 1N3893. 12FL	16FL	1N3879. 1N3883. 6FL	1N3889. 1N3893. 12FL	16FL	TEST CONDITIONS	UNITS	
	SINUSOI	DAL COND	UCTION	RECTANGULAR CONDUCTION					
180°	0.58	0.46	0.37	0.33	0.26	0.21		K/W	
120°	0.60	0.48	0.39	0.58	0.46	0.37	T.I = 150 °C		
60°	1.28	1.02	0.82	1.28	1.02	0.82	1j = 150 C		
30°	2.20	1.76	1.41	2.20	1.76	1.41			

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

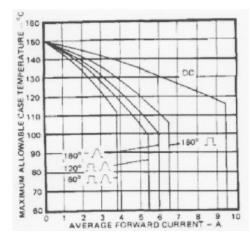


Fig. 1 - Average Forward Current vs. Maximum Allowable Case Temperature, 1N3879 and 6FL Series

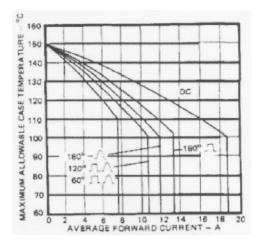
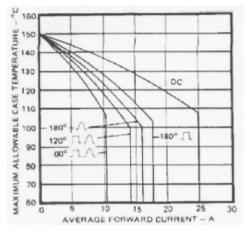


Fig. 2 - Average Forward Current vs. Maximum Allowable Case Temperature, 1N3889 and 12FL Series



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Fig. 3 - Average Forward Current vs. Maximum Allowable Case Temperature, 16FL Series

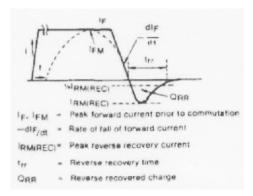


Fig. 4 - Reverse Recovery Time Test Waveform



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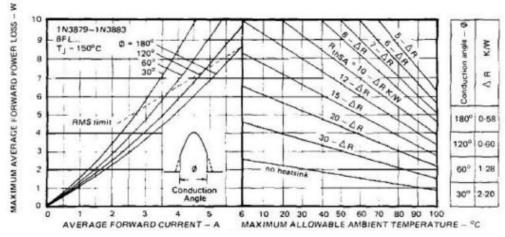
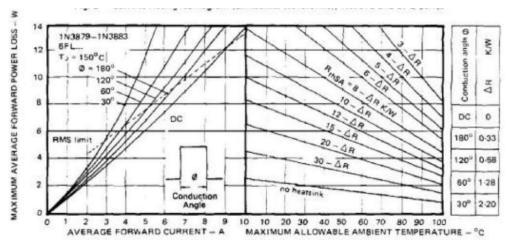
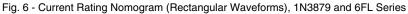
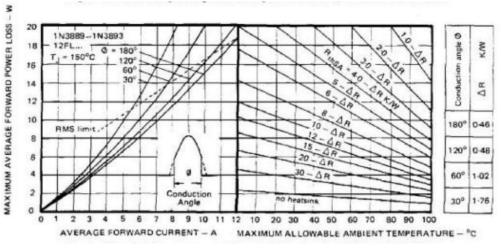
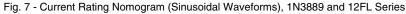


Fig. 5 - Current Rating Nomogram (Sinusoidal Waveforms), 1N3879 and 6FL Series









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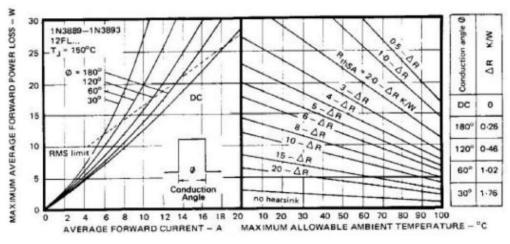


Fig. 8 - Current Rating Nomogram (Rectangular Waveforms), 1N3889 and 12FL Series

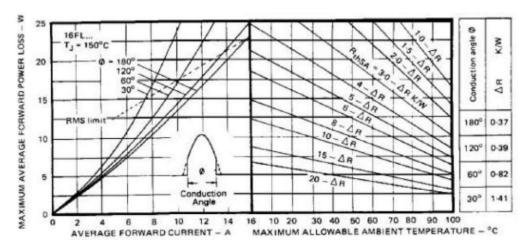
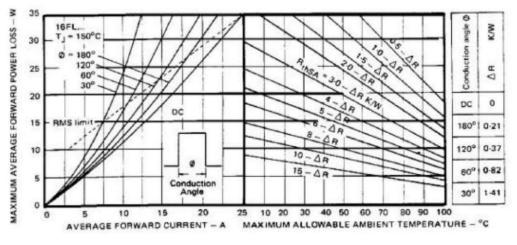


Fig. 9 - Current Rating Nomogram (Sinusoidal Waveforms), 16FL Series





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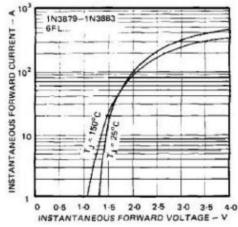


Fig. 11 - Maximum Forward Voltage vs. Forward Current, 1N3879 and 6FL Series

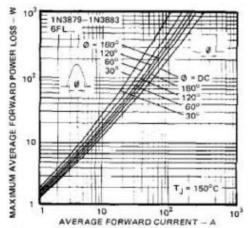


Fig. 12 - Maximum High Level Forward Power Loss vs. Average Forward Current, 1N3879 and 6FL Series

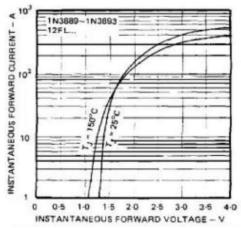


Fig. 13 - Maximum Forward Voltage vs. Forward Current, 1N3889 and 12FL Series

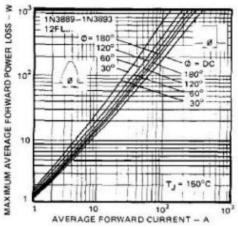
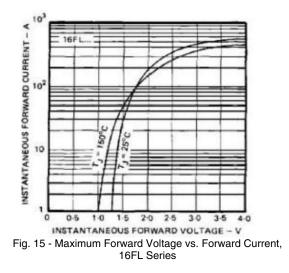
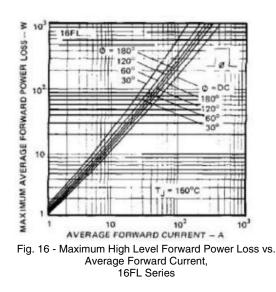


Fig. 14 - Maximum High Level Forward Power Loss vs. Average Forward Current, 1N3889 and 12FL Series





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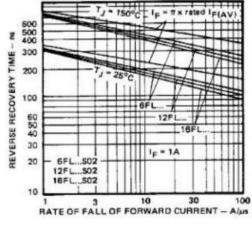


Fig. 17a - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, All Series ...S02

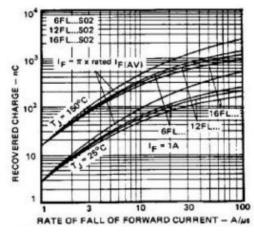
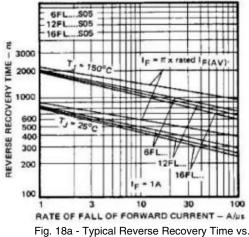


Fig. 17b - Typical Recovered Charge vs. Rate of Fall of Forward Current, All Series ...S02



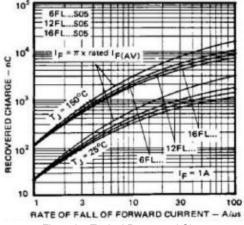
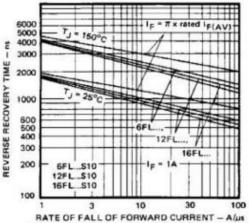
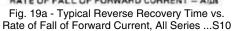
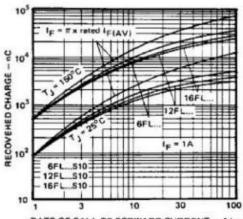
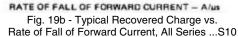


Fig. 18b - Typical Recovered Charge vs. Rate of Fall of Forward Current, All Series ...S05









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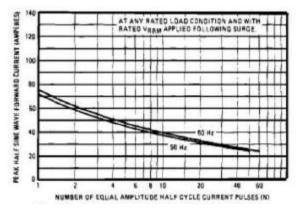
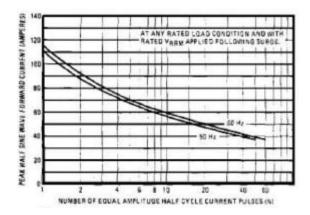
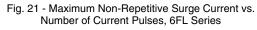


Fig. 20 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, 1N3879 Series





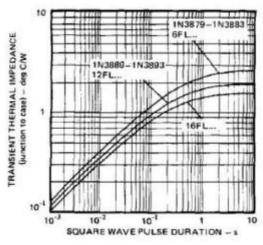
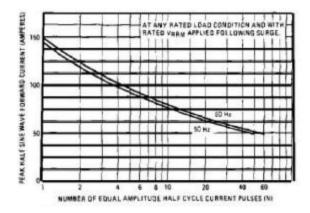
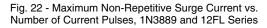


Fig. 24 - Maximum Transient Thermal Impedance, Junction to Case vs. Pulse Duration, All Series





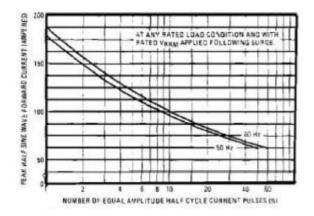


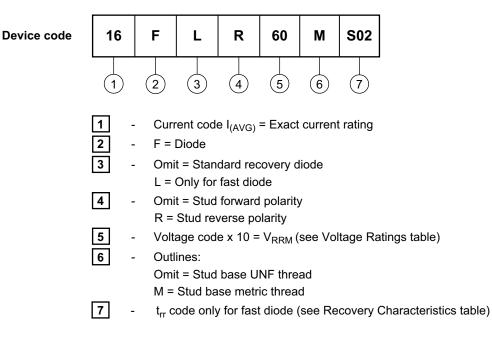
Fig. 23 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, 16FL Series

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ORDERING INFORMATION TABLE



LINKS TO RELATED DOCUMENTS						
Dimensions	http://www.vishay.com/doc?95311					

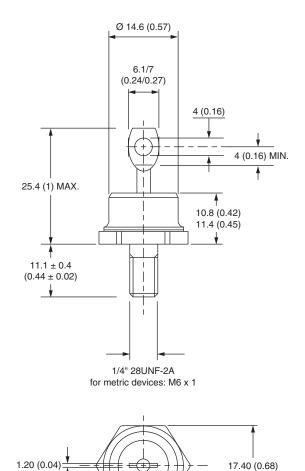


Vishay Semiconductors

DO-203AB (DO-5) for 40HFL, 70HFL and 85HFL

DIMENSIONS FOR 40HFL/70HFL in millimeters (inches)

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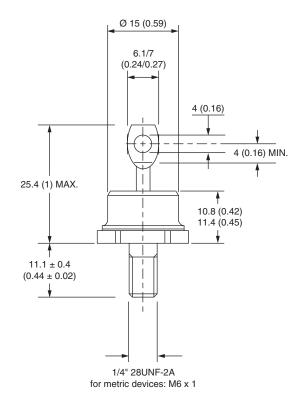


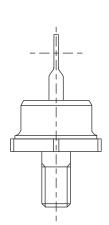


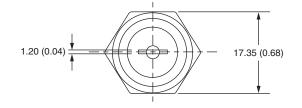
Vishay Semiconductors

DO-203AB (DO-5) for 40HFL, 70HFL and 85HFL

DIMENSIONS FOR 85HFL in millimeters (inches)









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